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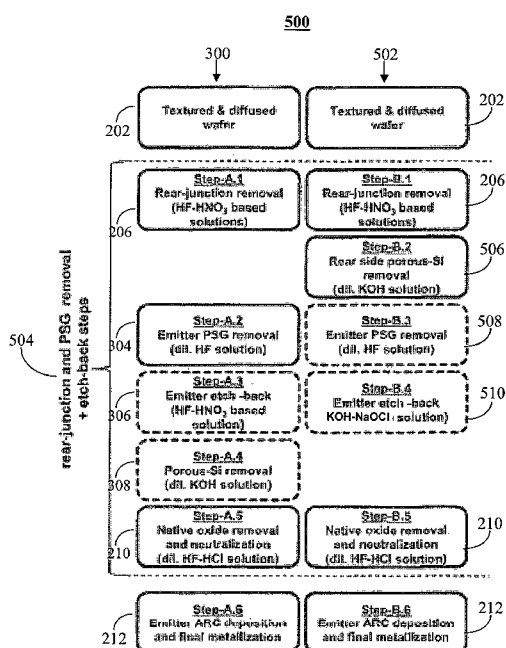
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- (54) **Title:** NON-ACIDIC ISOTROPIC ETCH-BACK FOR SILICON WAFER SOLAR CELLS



- (57) **Abstract:** A method for solar cell fabrication is provided. The method includes etching a doped surface of a silicon wafer solar cell using a solution including potassium hydroxide (KOH) and sodium hypochlorite (NaOCl). Alternatively the solution could include sodium hydroxide (NaOH) and NaOCl. In one aspect, the step of back-etching an emitter of the solar cell using the KOH:NaOCl solution is simultaneously performed with porous silicon removal. In another aspect, the step of back-etching the emitter of the solar cell using the KOH:NaOCl solution also includes PSG removal. And in yet another aspect, the step of back-etching the emitter of the solar cell using the KOH:NaOCl solution is performed simultaneously with polishing.



Declarations under Rule 4.17:

— *of inventorship (Rule 4.17(iv))*

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